

**IN THE CLAIMS:**

Please amend claims 1-5, 11 and 13 as follows:

1. (Currently Amended) A photomask for KrF excimer laser lithography having a shade film comprises a photosensitive polymer layer formed in a desired pattern on a quartz glass substrate, wherein the polymer layer is photosensitive to an electron beam, and the transmittance of the KrF excimer laser beam by the ~~shade film~~ polymer layer is 1% or less.
2. (Currently Amended) The photomask ~~as defined in~~ according to claim 1, wherein the transmittance of the KrF excimer laser beam by the shade film is 0.5% or less.
3. (Currently Amended) A photomask for KrF excimer laser lithography having an attenuator comprises a photosensitive polymer layer formed in a desired pattern on a quartz glass substrate, wherein the polymer layer is photosensitive to an electron beam, and the transmittance of the KrF excimer laser beam by the ~~attenuator~~ polymer layer ranges from 2% to 16%.
4. (Currently Amended) The photomask ~~as defined in~~ according to claim 3, wherein the transmittance of the KrF excimer laser beam by the ~~attenuator~~ polymer layer ranges from 4% to 9%.
5. (Currently Amended) The photomask ~~as defined in~~ according to claim 1, having a phase shifter for shifting a phase of the KrF excimer laser beam in a predetermined pattern by 180° on the quartz glass substrate.
6. (Withdrawn) A method for manufacturing a photomask with a transmittance of a KrF excimer laser beam by a shade film on a quartz glass substrate being 1% or less, comprising:  

forming a photosensitive polymer layer on the quartz glass substrate by irradiating either an activated light providing 40% or more of transmittance through

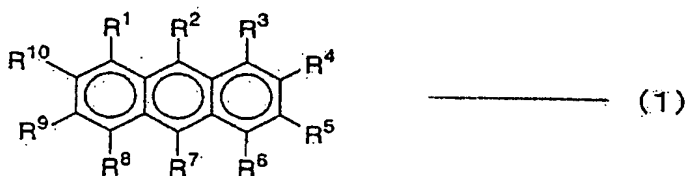
the polymer layer, or an electron beam; and

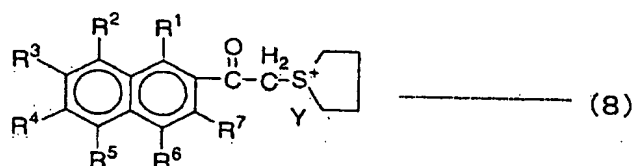
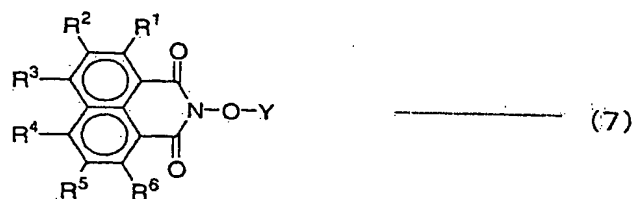
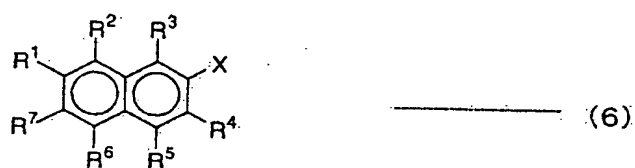
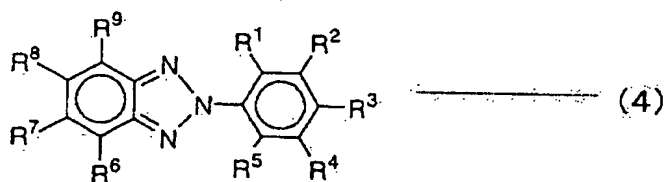
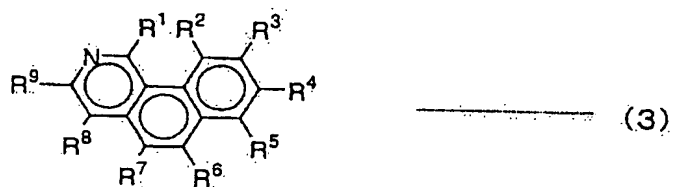
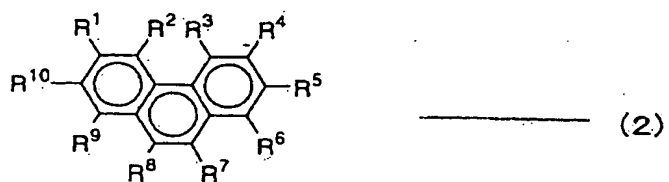
processing the irradiated polymer layer to render a desired pattern.

7. (Withdrawn) The method for manufacturing a photomask as defined in claim 6, wherein the transmittance of the KrF excimer laser beam by the shade film is 0.5% or less.
8. (Withdrawn) A method for manufacturing a half tone photomask for KrF excimer laser lithography, wherein an attenuator on a quartz glass substrate having a transmittance of a KrF excimer laser beam ranging from 2% to 16% is formed by forming a photosensitive polymer layer on the quartz glass substrate by irradiating either an activated light providing 40% or more of transmittance through the polymer layer, or an electron beam; and processing the irradiated polymer layer to render a desired pattern.
9. (Withdrawn) The method for manufacturing a photomask as defined in claim 8, wherein the transmittance of the KrF excimer laser by the attenuator ranges from 4% to 9%.
10. (Withdrawn) The method for manufacturing a photomask for KrF excimer laser lithography as defined in claim 6, further comprising a step of forming a phase shifter for shifting a phase of the KrF excimer laser beam in a predetermined pattern by 180° on the quartz glass substrate.
11. (Currently Amended) The photomask according to claim 1, wherein the photosensitive polymer layer contains light absorbent for KrF excimer laser.
12. (Original) The photomask according to claim 11, wherein the light absorbent is chemically bonded to composition of the photosensitive polymer layer.
13. (Currently Amended) The photomask according to claim 3, wherein the photosensitive polymer layer contains light absorbent for KrF excimer laser.

14. (Original) The photomask according to claim 13, wherein the light absorbent is chemically bonded to composition of the photosensitive polymer layer.
15. (Withdrawn) The method for manufacturing a photomask according to claim 6, wherein the photosensitive polymer layer contains absorbent for KrF excimer laser.
16. (Withdrawn) The method for manufacturing a photomask according to claim 15, wherein the light absorbent is chemically bonded to composition of the photosensitive polymer layer.
17. (Withdrawn) The method for manufacturing a photomask according to claim 8, wherein the photosensitive polymer layer contains absorbent for KrF excimer laser.
18. (Withdrawn) The method for manufacturing a photomask according to claim 17, wherein the light absorbent is chemically bonded to composition of the photosensitive polymer layer.
19. (Withdrawn) A photosensitive resin composition for manufacturing a photomask for KrF excimer laser lithography having a shade film comprises a photosensitive polymer layer formed in a desired pattern on a quartz glass substrate and having a transmittance of a KrF excimer laser beam by the shade film being 1% or less, wherein

the composition containing at least one of light absorbents represented by the following general formulae (1) - (8):





where  $R^1$  to  $R^{10}$  each represents an atom or atom group selected from the group consisting of hydrogen, a substituted or non-substituted alkyl group of 1 to 4 carbon atoms, halogen, a hydroxy group, a methylol group, a substituted or non-substituted alkoxy group of 1 to 4 carbon atoms, a hydroxyl group, a phenyl group, a

methoxy group, an ethoxyethyl group, a cyclopropyl group, an acetal group and an acetyl group,  $R^1$  to  $R^{10}$  being identical to or different from each other, X represents a halogenated acetyl group, and Y represents an atom or atom group selected from the group consisting of camphor sulfonate, trifluoro sulfonate and methane sulfonate.

20. (Withdrawn) The photosensitive resin composition as defined in claim 19, wherein the transmittance of the KrF excimer laser beam by the shade film is 0.5% or less.